TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT8G134

Strobe Flash Applications

- Compact and Thin (TSSOP-8) package •
- Enhancement-mode
- Peak collector current: $I_{C} = 150 \text{ A} (\text{max})$

(@VGE=2.5V(min))/

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	400	V	
Gate-emitter voltage	DC	V _{GES}	± 4	V	
	Pulse	V _{GES}	± 5		
Collector current	Pulse (Note 1)	I _{CP}	150	A	
Collector power dissipation (t=10 s)	(Note 2a)	P _C (1)	1.1	W	
	(Note 2b)	P _C (2)	0.6	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

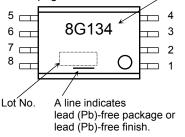
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

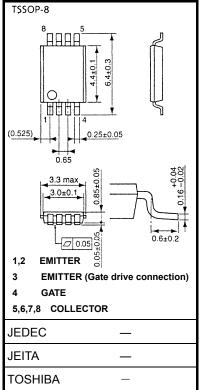
Thermal Characteristics

Characteristics	Symbol	Rating	Unit	
Thermal resistance , junction to ambient (t = 10 s) (Note2a)	R _{th (j-a)} (1)	114	°C/W	
Thermal resistance , junction to ambient (t = 10 s) (Note2b)	R _{th (j-a)} (2)	208	°C/W	

Marking (Note 3)

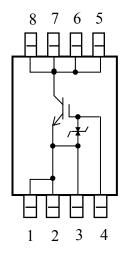
Note : For (Note 1), (Note 2a), (Note 2b) and (Note 3), Please refer to the next page. Part No. (or abbreviation code)





Weight: 0.035 g (typ.)

Circuit Configuration



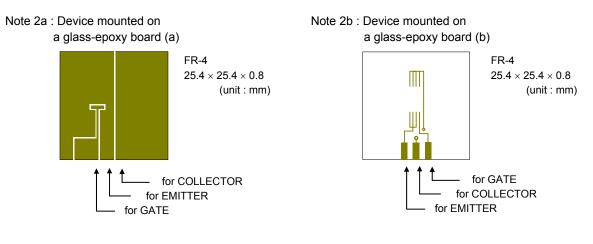
Unit: mm

Electrical Characteristics (Ta = 25°C)

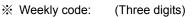
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	$V_{GE} = \pm 4 V$, $V_{CE} = 0$		_	± 10	μA
Collector cut-off current		ICES	$V_{CE} = 400 \text{ V}, \text{ V}_{GE} = 0$	_	_	10	μA
Gate-emitter cut-off voltage		V _{GE (OFF)}	$I_C = 1 \text{ mA}, V_{CE} = 5 \text{ V}$	0.65	1.0	1.35	V
Collector-emitter saturation voltage		V _{CE (sat)}	$I_C = 150 \text{ A}, \text{ V}_{GE} = 2.5 \text{ V}$	_	3.4	_	V
Input capacitance		Cies	$V_{CE}=10~V,~V_{GE}=0,~f=1~MHz$	_	4560	_	pF
Switching time	Rise time	tr	$\begin{array}{c} 3 \\ V \\ 0 \\ \hline \\ 0 \\ \hline \\ 0 \\ \hline \\ 0 \\ \hline \\ 62 \\ \Omega \\ \hline \\ \hline \\ \\ 0 \\ \hline 0 \\ \hline \\ 0 \\ \hline \\ 0 \\ \hline 0 \\ \hline \\ 0 \\ \hline 0 \\ $	_	0.6		μs
	Turn-on time	t _{on}		_	0.8		
	Fall time	t _f			1.2		
	Turn-off time	t _{off}		_	1.8		

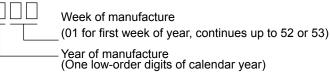
Note

Note 1: Please use devices on condition that the junction temperature is below 150°C. Repetitive rating: pulse width limited by maximum junction temperature.



Note 3: O on lower right of the marking indicates Pin 1.





※ Pb-Free Finish (Only a coating lead terminal) :

It is marking about an underline to a week of manufacture mark.



Caution on handling

This device is MOS gate type. Therefore , please care of a protection from ESD in your handling .

Caution in design

You should be design dV/dt value under Icp=150A is below 400 V/ μ s when IGBT turn off under Ta=70°C. You should be design to don't flow collector current through terminal number 3.

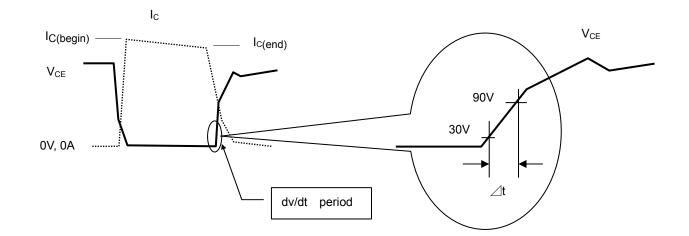
•definition of dv/dt

The slope of V_{CE} from 30v to 90v (attached figure.1)

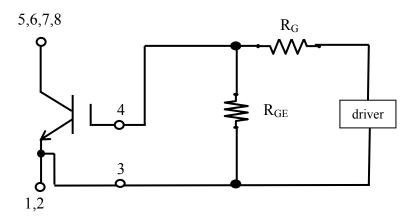
dv/dt = (90V-30V) / (∠t) = 60V / ∠t

waveform

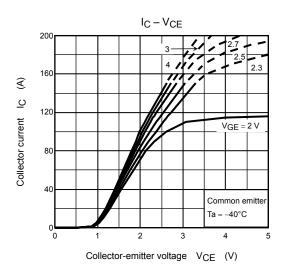
•waveform (expansion)

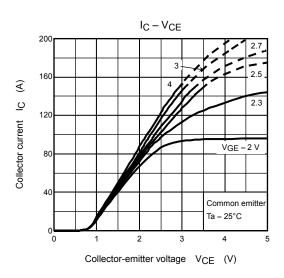


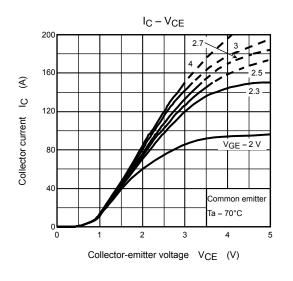
Gate drive connection

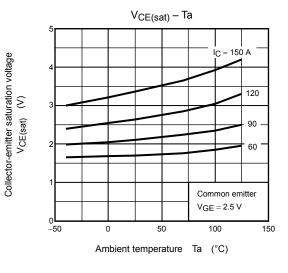


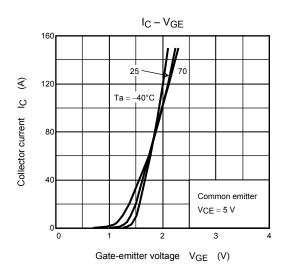
TOSHIBA

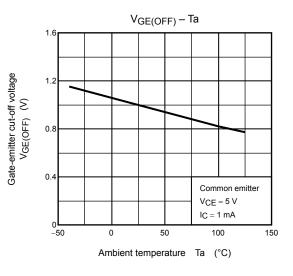




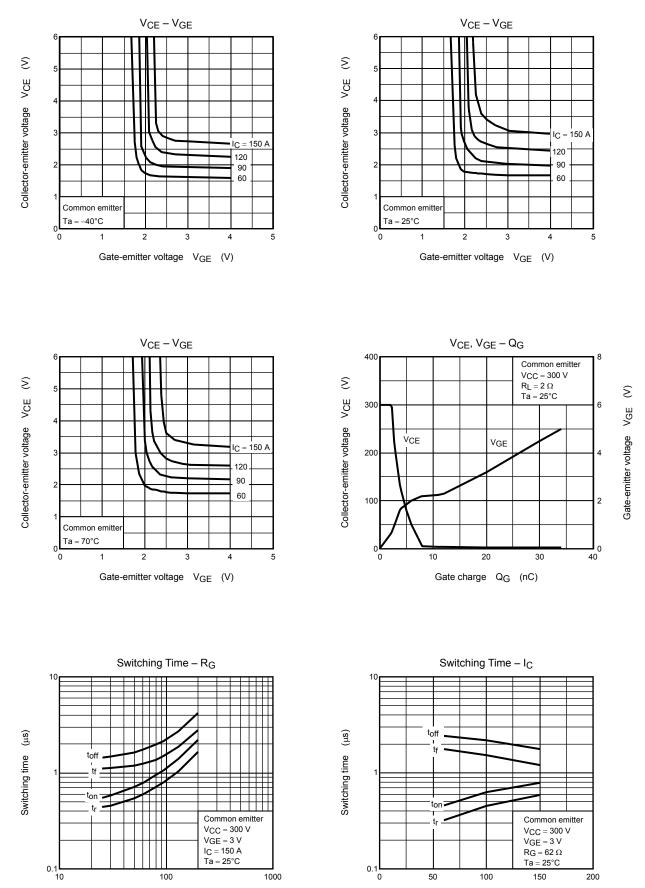






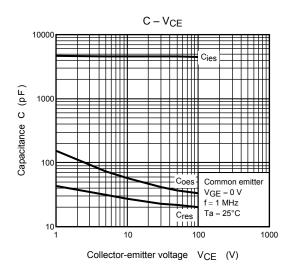


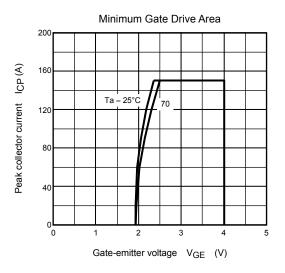
TOSHIBA

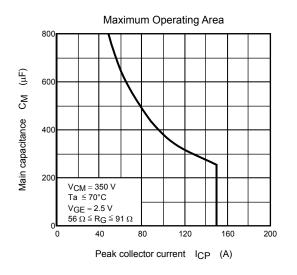


Gate resistance R_G (Ω)

TOSHIBA







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20070701-EN

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